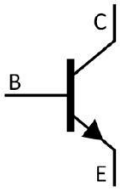


Rev. H Oct.-2018

Silicon NPN transistor in a TO-220 Plastic Package.

Complement to TIP42.

Medium power linear switching applications.

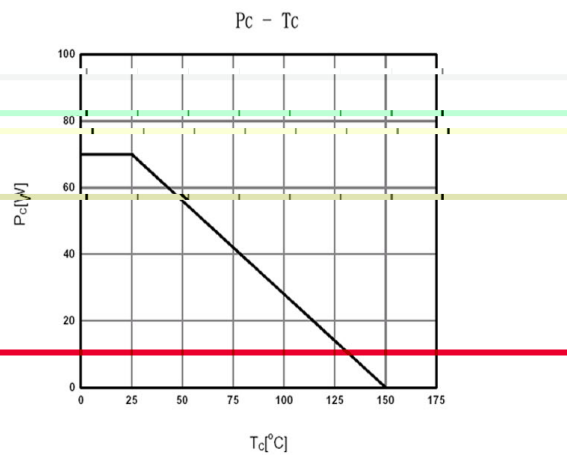
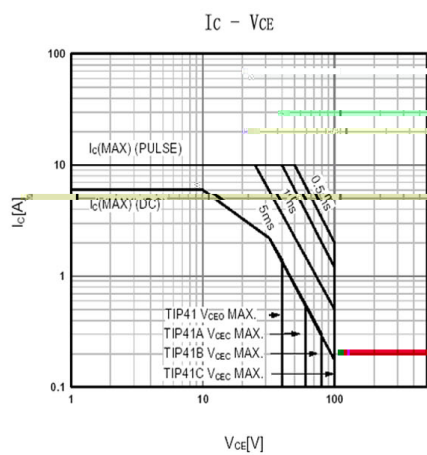
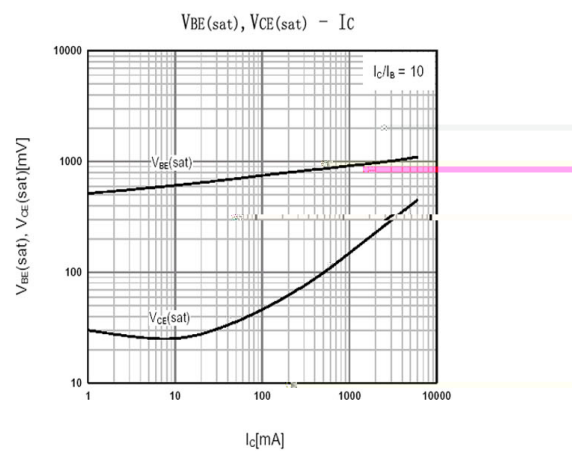
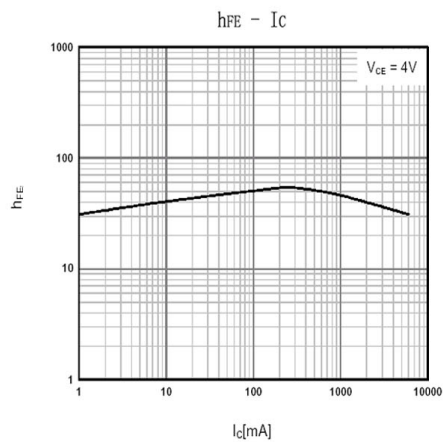


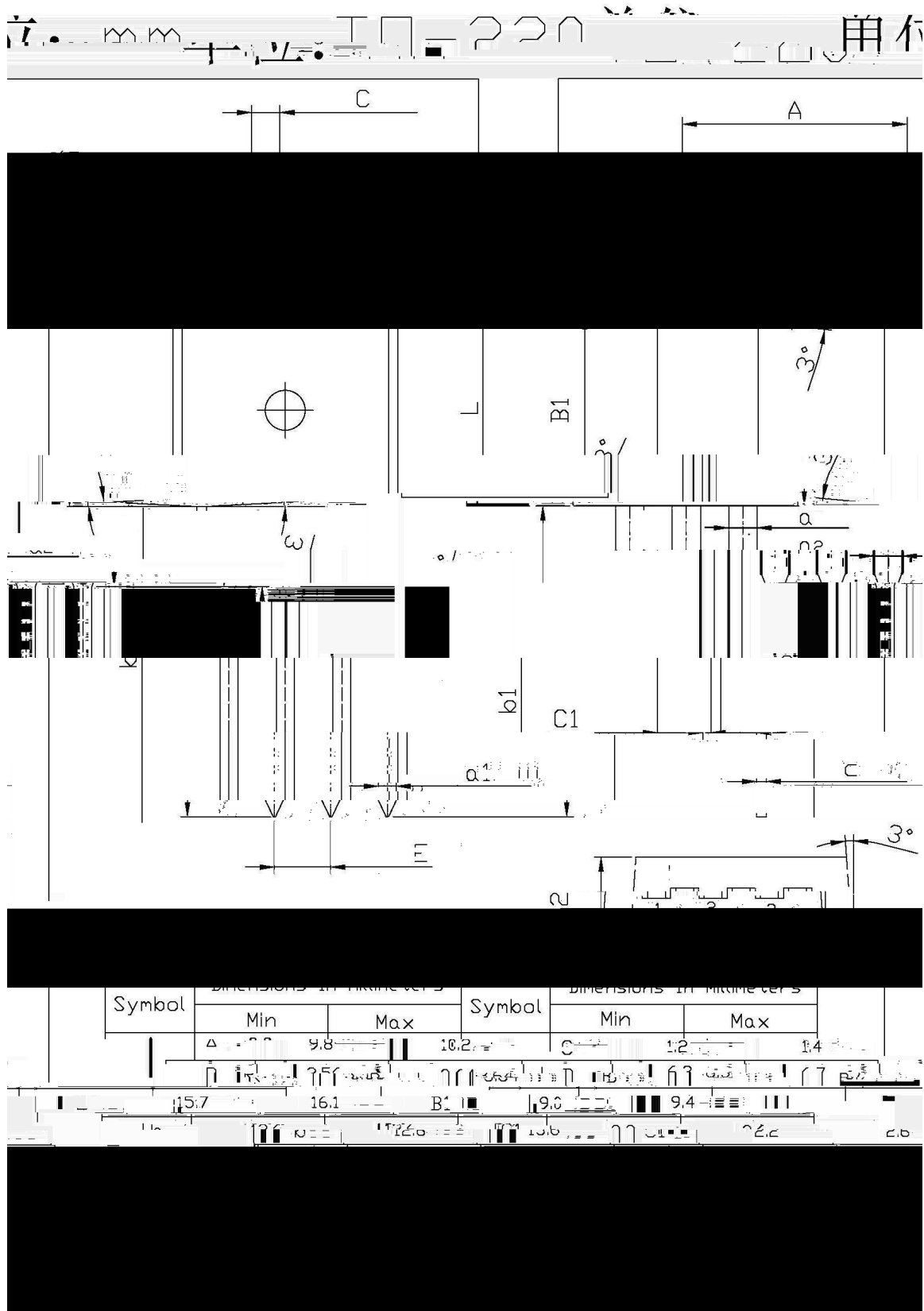
PIN1 Base PIN 2 Collector PIN 3 Emitter

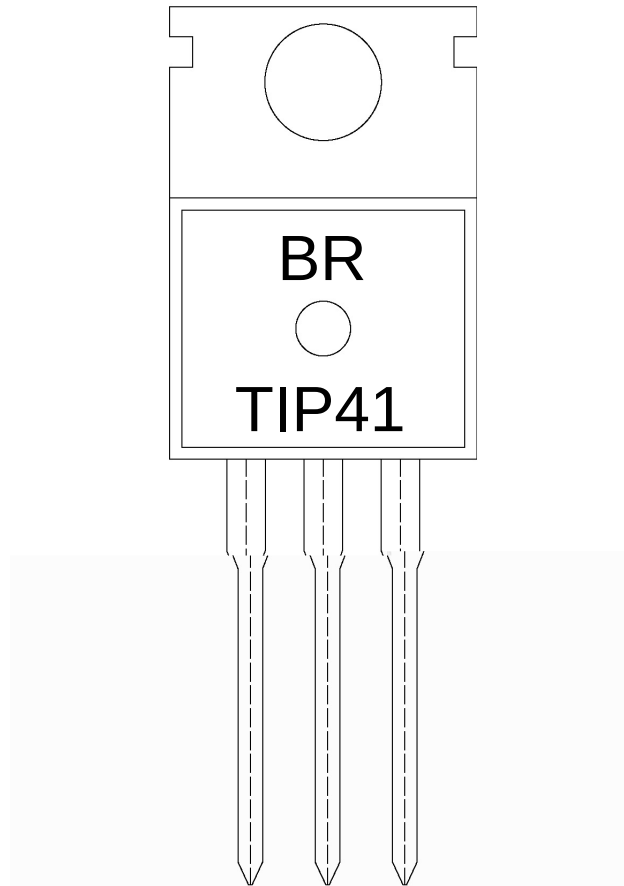
See Marking Instructions.

Parameter	Symbol	Rating				Unit
		TIP41	TIP41A	TIP41B	TIP41C	
Collector to Base Voltage	V_{CBO}	40	60	80	100	V
Collector to Emitter Voltage	V_{CEO}	40	60	80	100	V
Emitter to Base Voltage	V_{EBO}	5				V
Collector Current - Continuous	I_C	6				A
Peak Collector Current	I_{CP}	10				A
Base Current - Continuous	I_B	2				A
Collector Power Dissipation	P_C	2				W
Collector Power Dissipation	P_C ($T_c=25^\circ C$)	65				W
Junction Temperature	T_j	150				
Storage Temperature Range	T_{sag}	-55 150				

Parameter	Symbol		Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	TIP41	$I_C=30mA$ $I_B=0$	40			V
		TIP41A		60			
		TIP41B		80			
		TIP41C		100			
Collector Cut-Off Current	I_{CEO}	TIP41 TIP41A	$V_{CE}=30V$ $I_B=0$			0.7	mA
		TIP41B TIP41C	$V_{CE}=60V$ $I_B=0$				
Collector Cut-Off Current	I_{CES}	TIP41	$V_{CE}=40V$ $V_{EB}=0$			400	A
		TIP41A	$V_{CE}=60V$ $V_{EB}=0$				
		TIP41B	$V_{CE}=80V$ $V_{EB}=0$				
		TIP41C	$V_{CE}=100V$ $V_{EB}=0$				
Emitter Cut-Off Current	I_{EBO}		$V_{EB}=5V$ $I_C=0$			1	mA
DC Current Gain	$h_{FE(1)}$		$V_{CE}=4V$ $I_C=3A$	15		75	
	$h_{FE(2)}$		$V_{CE}=4V$ $I_C=0.3A$	30			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$		$I_C=6A$ $I_B=0.6A$			1.5	V
Base to Emitter Voltage	V_{BE}		$I_C=6A$ $V_{CE}=4V$			2	V
Transition Frequency	f_T		$V_{CE}=10V$ $I_C=500mA$	3			MHz





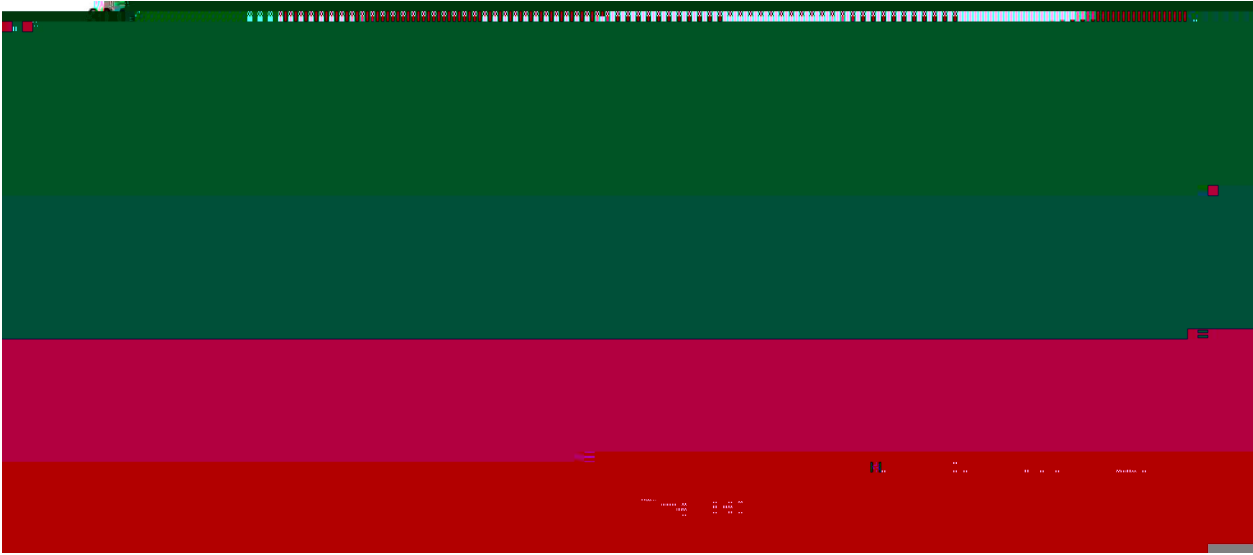


Note:

BR: Company Code

TIP41: Product Type.

****: Lot No. Code, code change with Lot No.



1

25 150

60 90sec;

Note:
1.Preheating:25~150